

WHAT IS CLAIMED IS:

1. A precision-of-register measuring mark, comprising:

a pair of register mark patterns spaced on a wafer; and

a resist pattern provided between the pair of register mark patterns and symmetrical in a direction of the arrangement of the pair of register mark patterns resulting from dual exposure.

2. A precision-of-register measuring mark according to Claim 1, wherein the resist pattern has a simple rectangular form.

3. A precision-of-register measuring method, comprising the steps of:

forming a resist film on a wafer having a pair of spaced mark patterns;

forming a first rendering pattern by rendering on the wafer a mask pattern symmetrical in the direction of the arrangement of the pair of mark patterns as a result of a first exposure in register with the register mark pattern;

forming a second rendering pattern by rendering on

the wafer the mask pattern as a result of a second exposure in register with the register mark pattern;

developing to form a resist pattern where the first rendering pattern and the second rendering pattern overlap; and

calculating the precision of register by $(X1+X2)/2 - (X3+X4)/2$ where, in the register direction of the mask patterns, the coordinate of one side of one of the pair of register mark patterns is $X1$, the coordinate of one side of the other of the pair of register mark patterns and symmetrical to the one side of the one register mark pattern is $X2$, and the coordinates of two sides of the resist pattern are $X3$ and $X4$.

4. A precision-of-register measuring method according to Claim 3, wherein the mark pattern has a simple rectangular form.